TOSHIBA 1R5JU41

TOSHIBA RECTIFIER SILICON DIFFUSED TYPE

1 R 5 J U 4 1

HIGH SPEED RECTIFIER APPLICATIONS (FAST RECOVERY)

• Average Forward Current : IF(AV)=1.5A

• Repetitive Peak Reverse Voltage: VRRM=600V

• Reverse Recovery Time : t_{rr}=100ns (Max.)

• Plastic Mold Type.

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak Reverse Voltage	V_{RRM}	600	V	
Average Forward Current	I _{F (AV)}	1.5	Α	
Peak One Cycle Surge Forward	Ingar	40 (50Hz)	A	
Current (Non-Repetitive)	I _{FSM}	44 (60Hz)		
Junction Temperature Range	$T_{ m j}$	-40~150	°C	
Storage Temperature Range	$T_{ m stg}$	-40~150	°C	

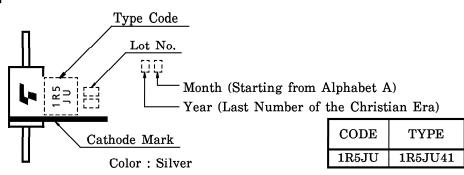
1. ANODE 2. CATHODE

JEDEC —
EIAJ —
TOSHIBA 3-4B1A

Unit in mm

Weight: 0.47g

MARKING



961001EAA2

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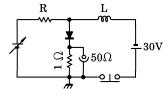
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

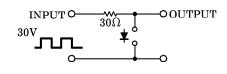
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	$V_{\mathbf{FM}}$	$V_{FM} = 2.0A$	_	_	2.0	V
Repetitive Peak Reverse Current	$I_{ m RRM}$	$V_{RRM} = 600V$	_	_	100	μ A
Reverse Recovery Time (Note 1)	t _{rr}	$I_{\rm F} = 1 {\rm A}, \; {\rm di} / {\rm dt} = -30 {\rm A} / \mu {\rm s}$	_	_	100	ns
Forward Recovery Time (Note 2)	tfr	I _F =1.0A	_	_	250	ns
Thermal Resistance (Note 3)	R _{th (j-a)}	Junction to Ambient	_		86	°C/W
Thermal Resistance (Note 3)	$R_{ ext{th}(j-\ell)}$	Junction to Lead	_	_	23	°C/W

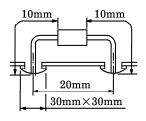
(Note 1) t_{rr} TEST CIRCUIT

(Note 2) t_{fr} TEST CIRCUIT

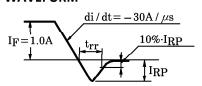
(Note 3) THERMAL RESISTANCE



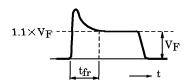




WAVEFORM



WAVEFORM



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